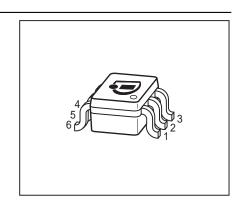


### **NPN Silicon RF Transistor\***

- For low noise, high-gain broadband amplifiers at collector currents from 2 mA to 30 mA
- $f_T$  = 8 GHz, F = 0.9 dB at 900 MHz
- Two (galvanic) internal isolated
  Transistor in one package
- For orientation in reel see package information below
- Pb-free (RoHS compliant) package 1)
- Qualified according AEC Q101
- \* Short term description





ESD (Electrostatic discharge) sensitive device, observe handling precaution!

Туре	Marking	Pin Configuration				Package		
BFS483	RHs	1=B	2=E	3=C	4=B	5=E	6=C	SOT363

<sup>&</sup>lt;sup>1</sup>Pb-containing package may be available upon special request



Maximum Ra
------------

Parameter	Symbol	Value	Unit	
Collector-emitter voltage	$V_{\sf CEO}$	12	V	
Collector-emitter voltage	$V_{CES}$	20		
Collector-base voltage	$V_{\mathrm{CBO}}$	20		
Emitter-base voltage	$V_{EBO}$	2		
Collector current	I <sub>C</sub>	65	mA	
Base current	I <sub>B</sub>	5		
Total power dissipation <sup>1)</sup>	P <sub>tot</sub>	450	mW	
T <sub>S</sub> ≤ 40 °C				
Junction temperature	$ T_{i} $	150	°C	
Ambient temperature	$  au_{A} $	-65 150		
Storage temperature	$T_{sta}$	-65 150		

## **Thermal Resistance**

Parameter	Symbol	Value	Unit
Junction - soldering point <sup>2)</sup>	R <sub>thJS</sub>	≤ 245	K/W

# **Electrical Characteristics** at $T_A$ = 25°C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics				,	
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	12	-	-	V
$I_{\rm C}$ = 1 mA, $I_{\rm B}$ = 0					
Collector-emitter cutoff current	I <sub>CES</sub>	-	-	100	μA
$V_{CE} = 20 \text{ V}, V_{BE} = 0$					
Collector-base cutoff current	I <sub>CBO</sub>	-	-	100	nA
$V_{\rm CB} = 10 \text{ V}, I_{\rm E} = 0$					
Emitter-base cutoff current	I <sub>EBO</sub>	-	-	1	μA
$V_{\rm EB}$ = 1 V, $I_{\rm C}$ = 0					
DC current gain-	h <sub>FE</sub>	70	100	140	-
$I_{\rm C}$ = 15 mA, $V_{\rm CE}$ = 8 V, pulse measured					

 $<sup>^{1}</sup>T_{\mathrm{S}}$  is measured on the collector lead at the soldering point to the pcb

 $<sup>^2\</sup>mbox{For calculation}$  of  $R_{\mbox{\scriptsize thJA}}$  please refer to Application Note Thermal Resistance



**Electrical Characteristics** at  $T_A = 25$ °C, unless otherwise specified Unit **Parameter Symbol Values** min. typ. max. AC Characteristics (verified by random sampling) 6 8 GHz Transition frequency  $f_{\mathsf{T}}$  $I_{\rm C}$  = 25 mA,  $V_{\rm CE}$  = 8 V, f = 500 MHz 0.34 0.54 pF Collector-base capacitance  $C_{cb}$  $V_{CR} = 10 \text{ V}, f = 1 \text{ MHz}, V_{BE} = 0$ , emitter grounded Collector emitter capacitance 0.13  $C_{ce}$  $V_{CF} = 10 \text{ V}, f = 1 \text{ MHz}, V_{BF} = 0$ , base grounded  $C_{\mathsf{eb}}$ 1.1 Emitter-base capacitance  $V_{EB} = 0.5 \text{ V}, f = 1 \text{ MHz}, V_{CB} = 0$ collector grounded F dB Noise figure  $I_{\rm C}$  = 5 mA,  $V_{\rm CE}$  = 8 V,  $Z_{\rm S}$  =  $Z_{\rm Sopt}$ , f = 900 MHz0.9  $I_{\rm C}$  = 5 mA,  $V_{\rm CF}$  = 8 V,  $Z_{\rm S}$  =  $Z_{\rm Sopt}$ , f = 1.8 GHz1.4 Power gain, maximum stable<sup>1)</sup> dB Gms 19  $I_{\rm C}$  = 15 mA,  $V_{\rm CF}$  = 8 V,  $Z_{\rm S}$  =  $Z_{\rm Sopt}$ ,  $Z_{\rm L}$  =  $Z_{\rm Lopt}$  , f = 900 MHz $G_{ma}$ 12.5 dB Power gain, maximum available<sup>2)</sup>  $I_{\rm C}$  = 15 mA,  $V_{\rm CE}$  = 8 V,  $Z_{\rm S}$  =  $Z_{\rm Sopt}$ ,  $Z_{\rm L}$  =  $Z_{\rm Lopt}$  , f = 1.8 GHz $|S_{21e}|^2$ Transducer gain dB  $I_{\rm C}$  = 15 mA,  $V_{\rm CE}$  = 8 V,  $Z_{\rm S}$  =  $Z_{\rm L}$  = 50  $\Omega$ , *f* = 900 MHz 15.5  $I_{\rm C}$  = 15 mA,  $V_{\rm CE}$  = 8 V,  $Z_{\rm S}$  =  $Z_{\rm I}$  = 50  $\Omega$ , f = 1.8 MHz10

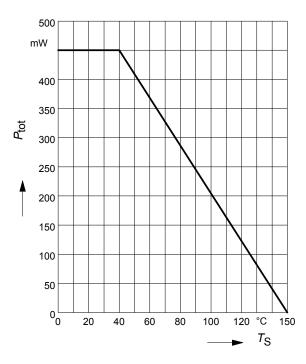
 $<sup>^{1}</sup>G_{\text{ms}} = |S_{21} / S_{12}|$ 

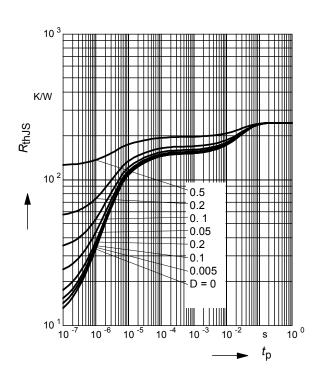
 $<sup>{}^{2}</sup>G_{\text{ma}} = |S_{21e}/S_{12e}| (k-(k^{2}-1)^{1/2})$ 



# Total power dissipation $P_{tot} = f(T_S)$

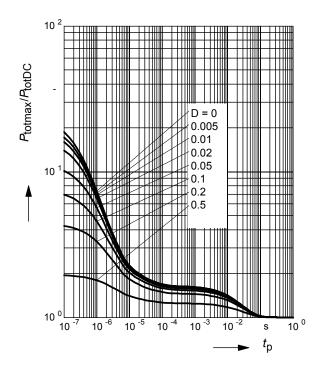
# Permissible Pulse Load $R_{thJS} = f(t_p)$





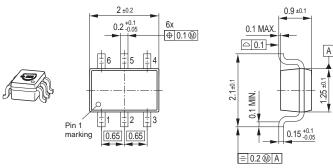
## **Permissible Pulse Load**

$$P_{\text{totmax}}/P_{\text{totDC}} = f(t_{\text{p}})$$

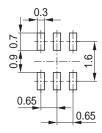




## Package Outline

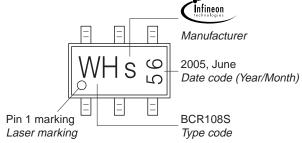


#### Foot Print



# Marking Layout (Example)

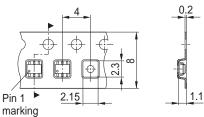
Small variations in positioning of Date code, Type code and Manufacture are possible.



# Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel Reel ø330 mm = 10.000 Pieces/Reel

For symmetric types no defined Pin 1 orientation in reel.





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